

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	2N3772
▶ Overseas	Part Number	2N3772
▶ Equivalent	Part Number	2N3772

EV is the abbreviation of name EVVO

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

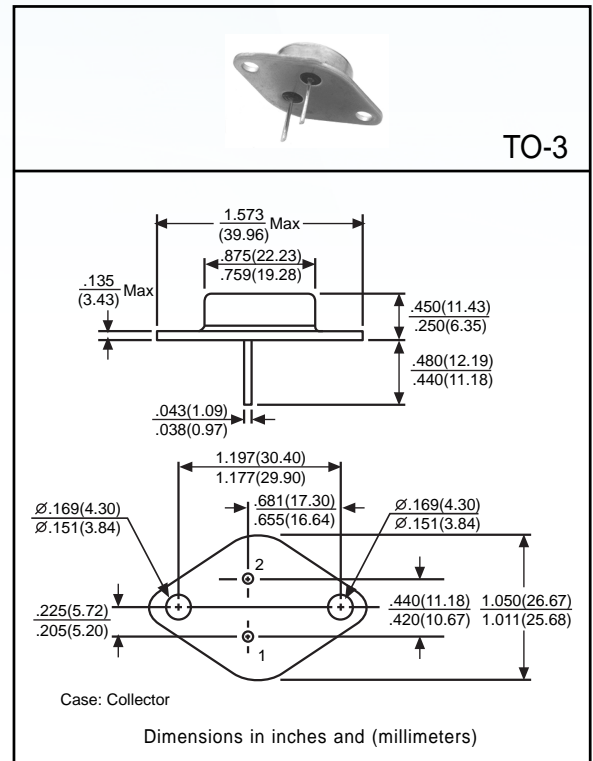
Designed for linear amplifiers, series pass regulators, and inductive switching applications.

Pinning

1 = Base
 2 = Emitter
 Case = Collector

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	100	V
Collector-Emitter Voltage	V_{CEO}	60	V
	V_{CEX}	80	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current (continuous)	I_C	30	A
Collector Current (peak)	I_C	30	A
Total Power Dissipation($T_C=25^{\circ}\text{C}$)	P_D	150	W
Junction Temperature	T_J	+200	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-65 to +200	$^{\circ}\text{C}$



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	60	-	-	V	$I_C=0.2A, I_B=0$
	$V_{CEX(sus)}$	80	-	-	V	$I_C=0.2A, V_{BE(off)}=1.5V, R_{BE}=100\Omega$
	$V_{CER(sus)}$	70	-	-	V	$I_C=0.2A, R_{BE}=100\Omega$
Collector Cutoff Current	I_{CEO}	-	-	10	mA	$V_{CE}=50V, I_B=0$
	I_{CEX}	-	-	5	mA	$V_{CE}=100V, V_{BE(off)}=1.5V$
		-	-	10	mA	$V_{CE}=30V, V_{BE(off)}=1.5V, T_C=150^{\circ}\text{C}$
Emitter Cutoff Current	I_{CBO}	-	-	5	mA	$V_{CB}=50V, I_E=0$
Collector-Emitter Saturation Voltage ⁽¹⁾	$V_{CE(sat)1}$	-	-	1.4	V	$I_C=10A, I_B=1.5A$
	$V_{CE(sat)2}$	-	-	4	V	$I_C=20A, I_B=4A$
Base-Emitter On Voltage ⁽¹⁾	$V_{BE(on)}$	-	-	2.2	V	$I_C=10A, V_{CE}=4V$
DC Current Gain ⁽¹⁾	h_{FE1}	15	-	60	-	$I_C=10A, V_{CE}=4V$
	h_{FE2}	5	-	-	-	$I_C=20A, V_{CE}=4V$
Second Breakdown Collector with Base Forward Bias	$I_{s/b}$	2.5	-	-	A	$V_{CE}=60V, t=1.0s, \text{Non-repetitive}$
Current Gain - Bandwidth Product	f_T	0.2	-	-	MHz	$I_C=1A, V_{CE}=4V, f=50\text{KHz}$
Small-Signal Current Gain	h_{fe}	40	-	-	-	$I_C=1A, V_{CE}=4V, f=1\text{KHz}$

(1) Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

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